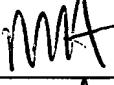


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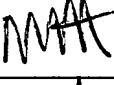
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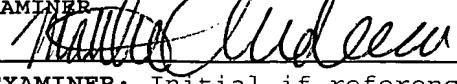
Examiner Initial		Document Number							Date	Name	Class	Subclass	Filing Date if Appropriate
	AA	5	8	6	8	8	3	7	February 9, 1999	DiSalvo et al.			
	AB												
	AC												
	AD												

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL	102 5 6 6 6 2	September 25, 1998	Japan			ABST.	
	AM	2000327 4 9 5	November 28, 2000	Japan			ABST.	
	AN	20002 2 2 1 2	January 21, 2000	Japan			ABST.	
	AO	20001 2 9 0 0	January 14, 2000	Japan			ABST.	

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	AP	Shuji NAKAMURA et al. "InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices", pp. L1568-L1571.
	AQ	Shuji NAKAMURA et al. "InGaN/GaN/AlGaN-Based Laser Diodes with Laser Diodes with Cleaved Facets Grown on GaN Substrates", pp. 832-834.
	AR	Sylwester POROWSKI, "Bulk and Homoepitaxial GaN-growth and Characterisation", pp. 153-158.
	AS	Hisanori YAMANE et al. "Preparation of GaN Single Crystal Using a Na Flux", pp. 413-416.
	AS	Appln. Serial No. 09/590,063 filed June 8, 2000

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